## NSN 5961-01-131-6636



Transistor - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5961-01-131-6636 **Inclosure Material:** Metal **Overall Length:** 1.252 inches **Overall Height:** Between 0.250 inches and 0.340 inches Overall Width: 0.700 inches **End Application:** An/fsq-114 11982 **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 90.0 breakdown voltage, collector-to-base, emitter open and 80.0 breakdown voltage, collector-to-emitter, base open and 7.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** Between 2.00 amperes source cutoff current and 4.00 amperes source cutoff current **Power Rating Per Characteristic:** 50.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 1 case and 2 pin Shelf Life: N/a

No

**Unit Of Measure:** 

Demilitarization:

## **NSN 5961-01-131-6636** Transistor - Page 2 of 2



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